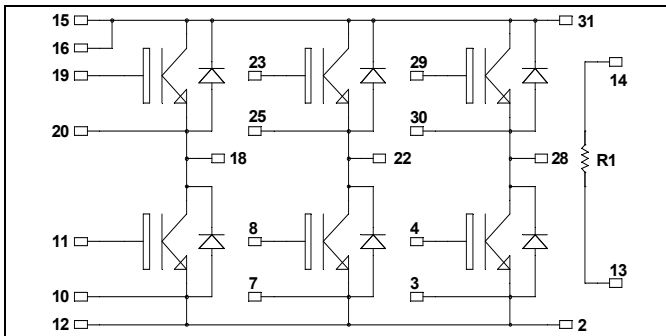
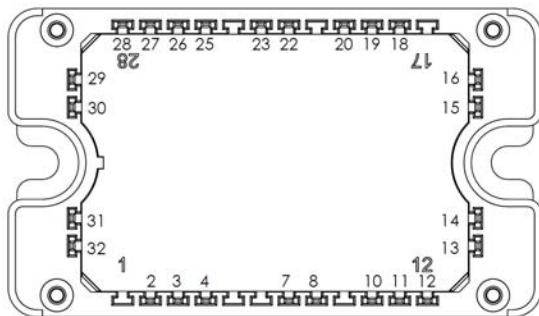


**3 Phase bridge
Trench + Field Stop IGBT3
Power Module**

**$V_{CES} = 600V$
 $I_C = 75A^* @ T_c = 80^\circ C$**



It is recommended to connect a decoupling capacitor between pins 31 & 2 to reduce switching overvoltages, if DC Power is connected between pins 15, 16 & 12. Pins 15 & 16 must be shorted together.



Application

- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$ 100*	A
		$T_C = 80^\circ C$ 75*	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$ 150	
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Power Dissipation	$T_C = 25^\circ C$ 250	W
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150^\circ C$ 150A @ 550V	

* Specification of IGBT device but output current must be limited due to size of output pin.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 75A$		$T_j = 25^\circ C$ 1.5 $T_j = 150^\circ C$ 1.7	1.9	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600\mu A$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

Dynamic Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$		4620		pF
C_{oes}	Output Capacitance			300		
C_{res}	Reverse Transfer Capacitance			140		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($25^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 75A$ $R_G = 4.7\Omega$		110		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
T_f	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($150^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 75A$ $R_G = 4.7\Omega$		120		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
T_f	Fall Time			60		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 75A$ $R_G = 4.7\Omega$		0.6		mJ
E_{off}	Turn-off Switching Energy	$T_j = 150^\circ C$ $^2T_j = 150^\circ C$		2.6		mJ
R_{thJC}	Junction to Case Thermal Resistance				0.6	$^\circ C/W$

Reverse diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage				600	V
I_{RM}	Reverse Leakage Current	$V_R = 600V$			250	μA
I_F	DC Forward Current	$T_c = 80^\circ C$		50		A
V_F	Diode Forward Voltage	$I_F = 50A$ $V_{GE} = 0V$		$T_j = 25^\circ C$ 1.6 $T_j = 150^\circ C$ 1.5	2	V
t_{rr}	Reverse Recovery Time	$I_F = 50A$ $V_R = 300V$ $di/dt = 1800A/\mu s$		$T_j = 25^\circ C$ 100 $T_j = 150^\circ C$ 150		ns
Q_{rr}	Reverse Recovery Charge			$T_j = 25^\circ C$ 2.6 $T_j = 150^\circ C$ 5.4		μC
E_r	Reverse Recovery Energy			$T_j = 25^\circ C$ 0.6 $T_j = 150^\circ C$ 1.2		mJ
R_{thJC}	Junction to Case Thermal Resistance				1.42	$^\circ C/W$

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

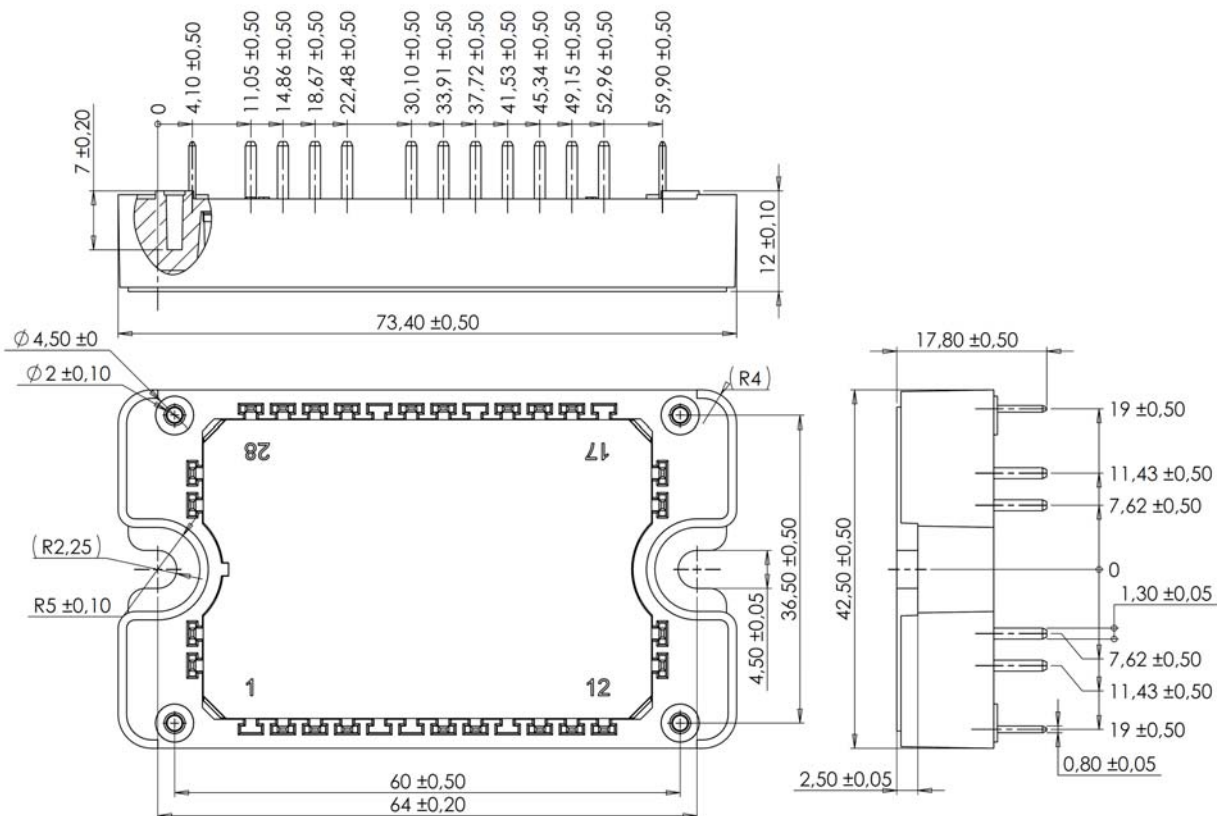
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

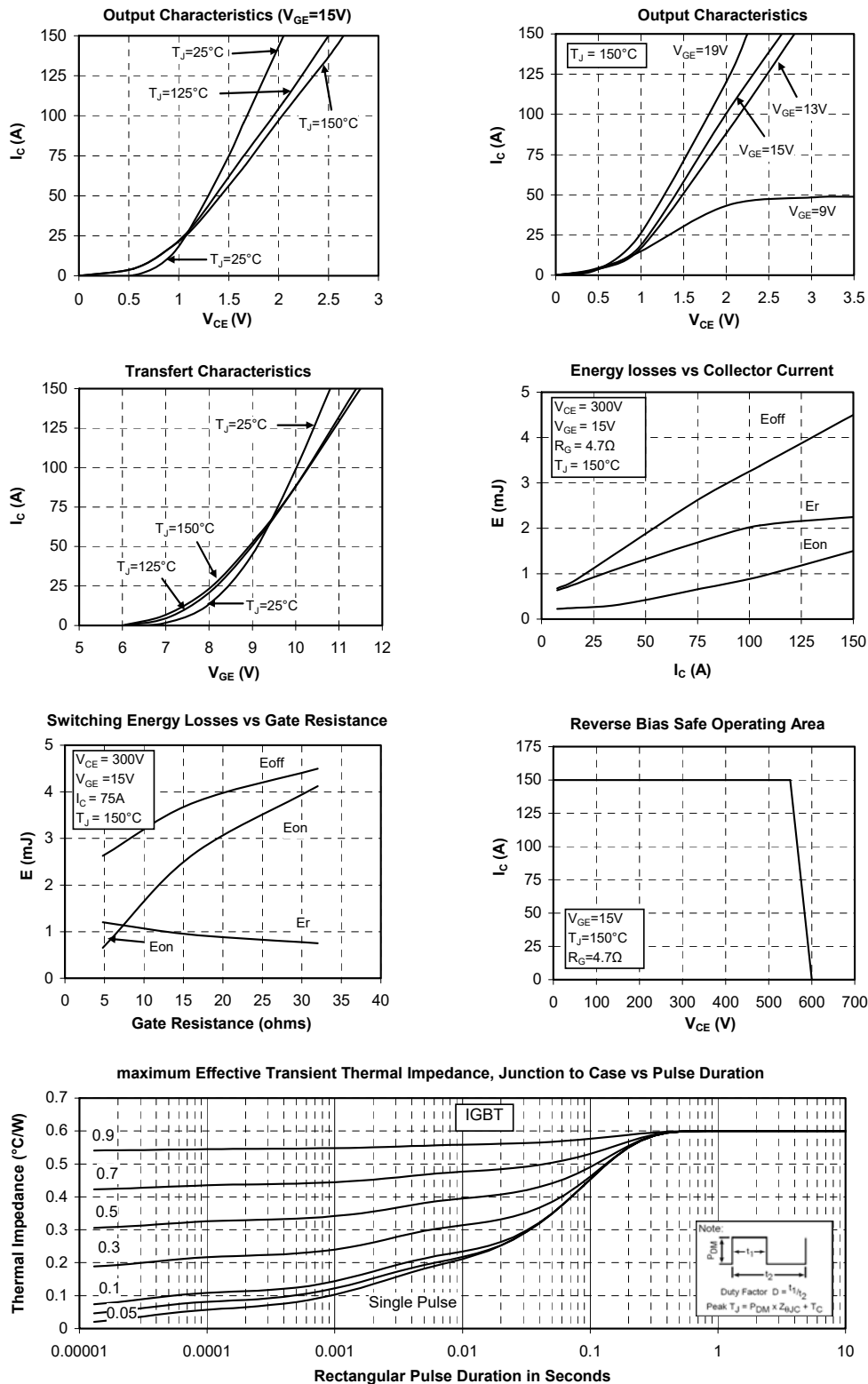
Symbol	Characteristic	Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz	4000		V
T _J	Operating junction temperature range	-40	175	°C
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} - 25	
T _{STG}	Storage Temperature Range	-40	125	
T _C	Operating Case Temperature	-40	100	
Torque	Mounting torque	To heatsink	M4	N.m
Wt	Package Weight		110	g

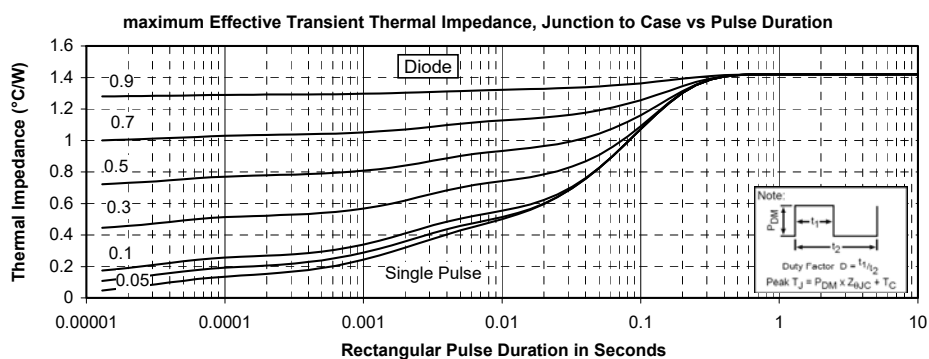
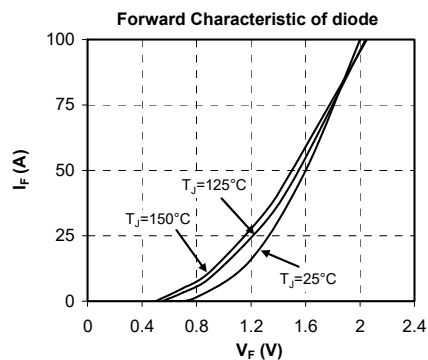
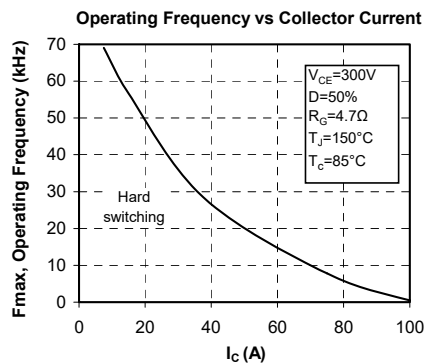
Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

Typical Performance Curve





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